

HIGH VOLTAGE SWITCHING APPLICATIONS

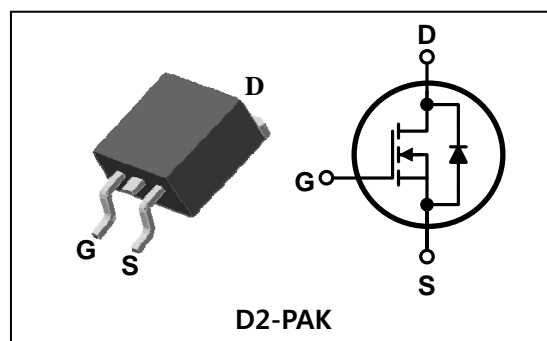
Features

- High Voltage : $BV_{DSS}=200V(\text{Min.})$
- Low C_{RSS} : $C_{RSS}=55pF(\text{Typ.})$
- Low gate charge : $Qg=22nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=0.17\Omega(\text{Max.})$

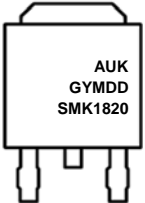
Ordering Information

Type No.	Marking	Package Code
SMK1820D2	SMK1820	D2-PAK

PIN Connection



Marking Diagram

	<p>Column 1 : Manufacturer</p> <p>Column 2 : Production Information e.g.) GYMDD</p> <ul style="list-style-type: none"> - . G : Factory management code - . YMDD : Date Code (year, month, date) <p>Column 3 : Device Code</p>
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Absolute maximum ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	V_{DSS}	200	V	
Gate-source voltage	V_{GSS}	± 30	V	
Drain current (DC) *	I_D	$T_C=25^\circ\text{C}$	18	A
		$T_C=100^\circ\text{C}$	11.4	A
Drain current (Pulsed) *	I_{DM}	72	A	
Power dissipation	P_D	100	W	
Avalanche current (Single) ②	I_{AS}	18	A	
Single pulsed avalanche energy ②	E_{AS}	453	mJ	
Avalanche current (Repetitive) ①	I_{AR}	18	A	
Repetitive avalanche energy ①	E_{AR}	13.9	mJ	
Junction temperature	T_J	150	$^\circ\text{C}$	
Storage temperature range	T_{stg}	-55~150		

* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	Junction-case	-	1.25	$^\circ\text{C}/\text{W}$
	Junction-ambient	-	62.5	

Electrical Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Drain-source breakdown voltage	BV _{DSS}	I _D =250uA, V _{GS} =0V	200	-	-	V	
Gate threshold voltage	V _{GS(th)}	I _D =250uA, V _{DS} =V _{GS}	2.0	-	4.0	V	
Drain-source cut-off current	I _{DSS}	V _{DS} =200V, V _{GS} =0V	-	-	1	uA	
		V _{DS} =160V, T _C =125°C	-	-	10		
Gate leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V	-	-	±100	nA	
Drain-source on-resistance ④	R _{DS(on)}	V _{GS} =10V, I _D =9.0A	-	0.14	0.17	Ω	
Forward transfer conductance ④	g _{fs}	V _{DS} =10V, I _D =9.0A	-	10.5	-	S	
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V f=1 MHz	-	942	1240	pF	
Output capacitance	C _{oss}		-	227	310		
Reverse transfer capacitance	C _{rss}		-	55	71		
Turn-on delay time	t _{d(on)}	V _{DD} =100V, I _D =18A R _G =25Ω	-	15	-	ns	
Rise time	t _r		-	130	-		
Turn-off delay time	t _{d(off)}		③④	-	135		-
Fall time	t _f		-	105	-		
Total gate charge	Q _g	V _{DS} =160V, V _{GS} =10V I _D =18A	-	22	28	nC	
Gate-source charge	Q _{gs}		③④	-	6.6		-
Gate-drain charge	Q _{gd}		-	-	7.2		-

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I _S	Integral reverse diode in the MOSFET	-	-	18	A
Source current (Pulsed) ①	I _{SM}		-	-	72	
Forward voltage ④	V _{SD}	V _{GS} =0V, I _S =18A	-	-	1.4	V
Reverse recovery time	t _{rr}	I _S =18A, V _{GS} =0V dI _F /dt=100A/us	-	208	-	ns
Reverse recovery charge	Q _{rr}		-	1.63	-	uC

Note ;

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=2.1mH, I_{AS}=18A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
- ③ Pulse Test : Pulse width≤300us, Duty cycle≤2%
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

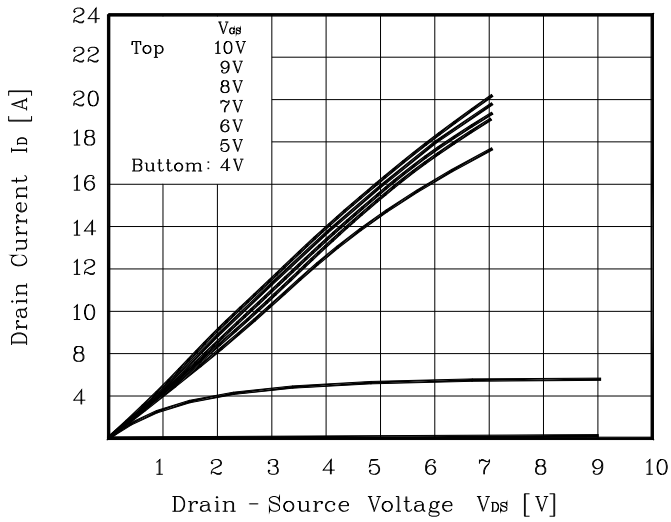


Fig. 2 $I_D - V_{GS}$

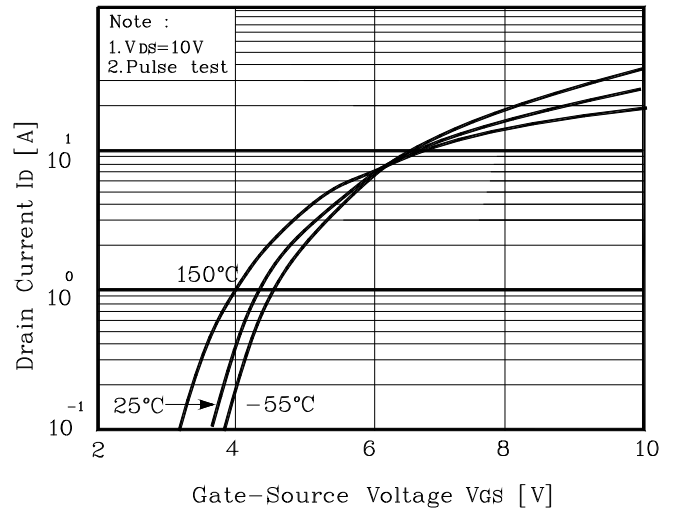


Fig. 3 $R_{DS(on)} - I_D$

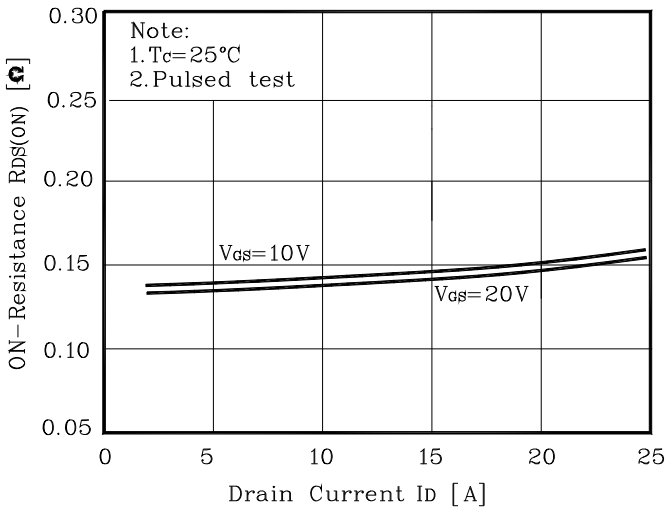


Fig. 4 $I_S - V_{SD}$

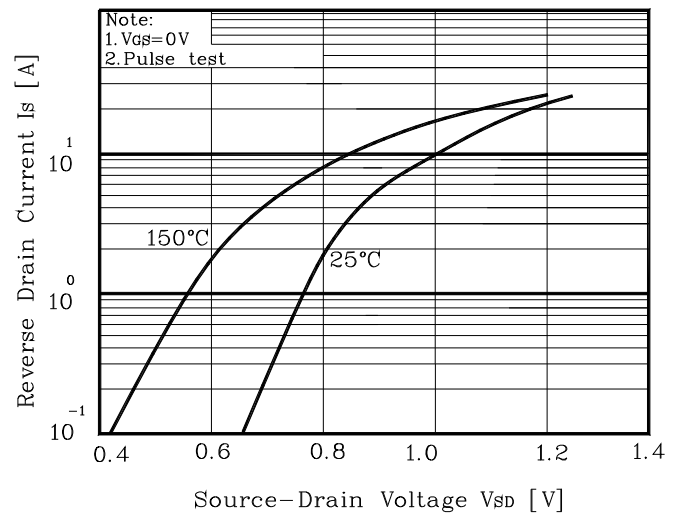


Fig. 5 Capacitance - V_{DS}

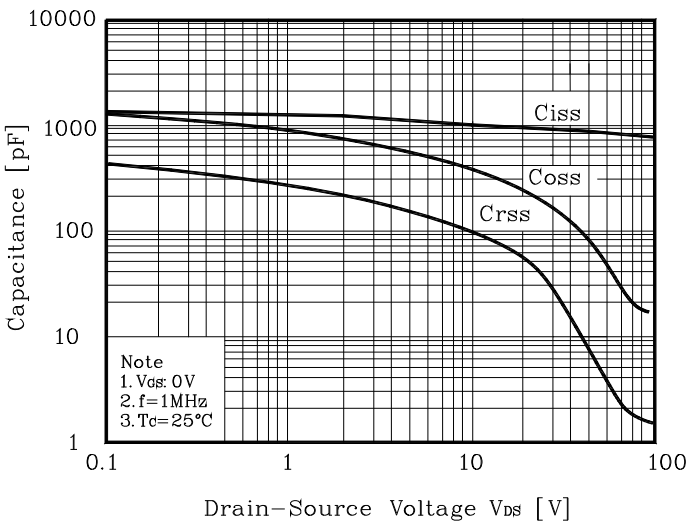


Fig. 6 $V_{GS} - Q_g$

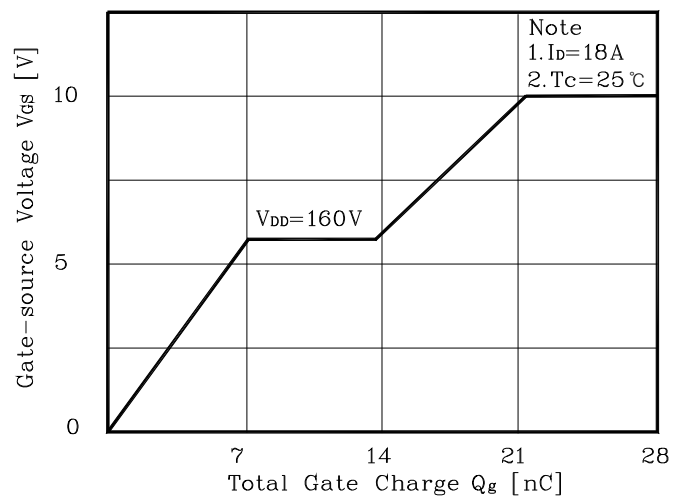


Fig. 7 $V_{DSS} - T_J$

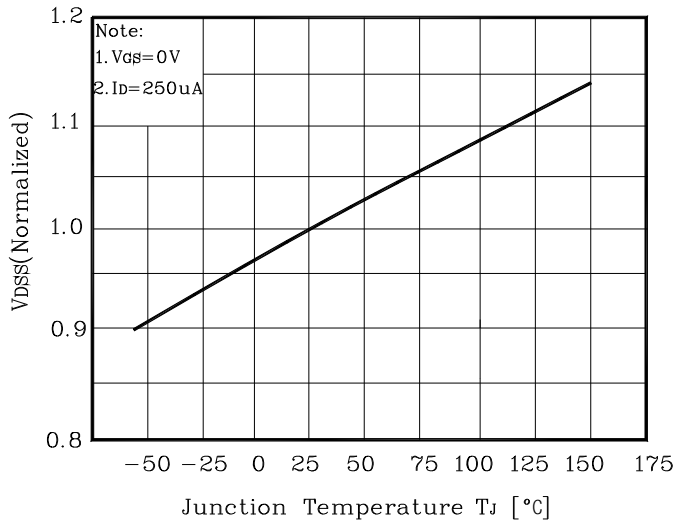


Fig. 8 $R_{DS(on)} - T_J$

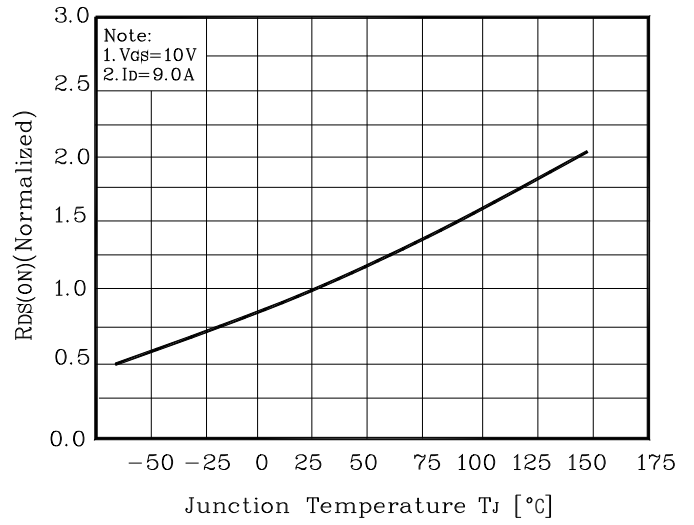


Fig. 9 $I_D - T_C$

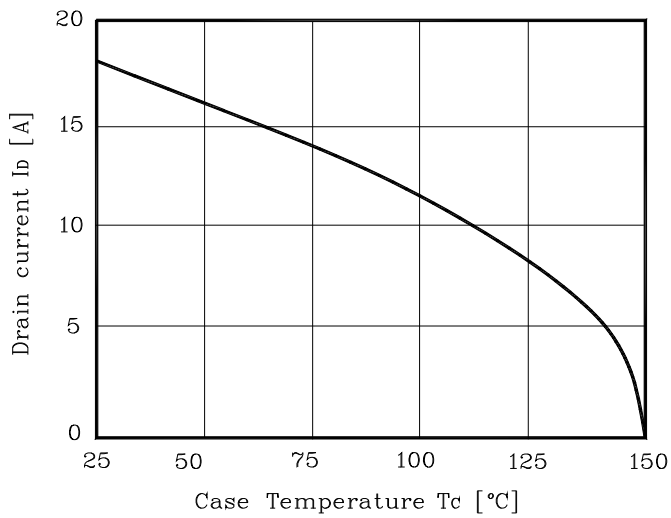


Fig. 10 Safe Operating Area

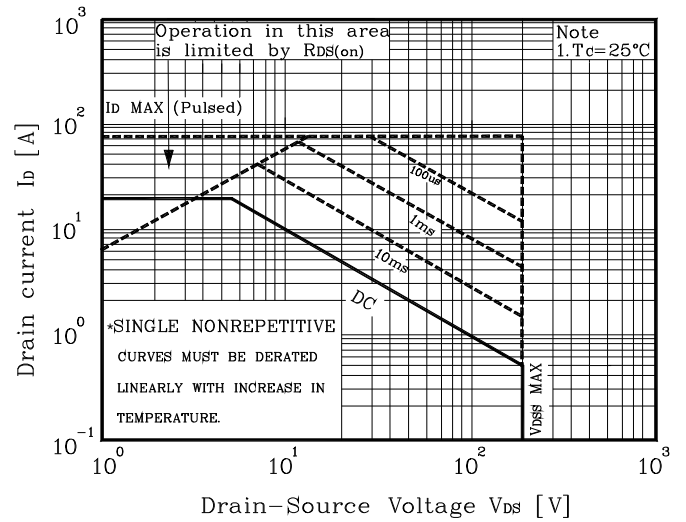


Fig. 11 Gate Charge Test Circuit & Waveform

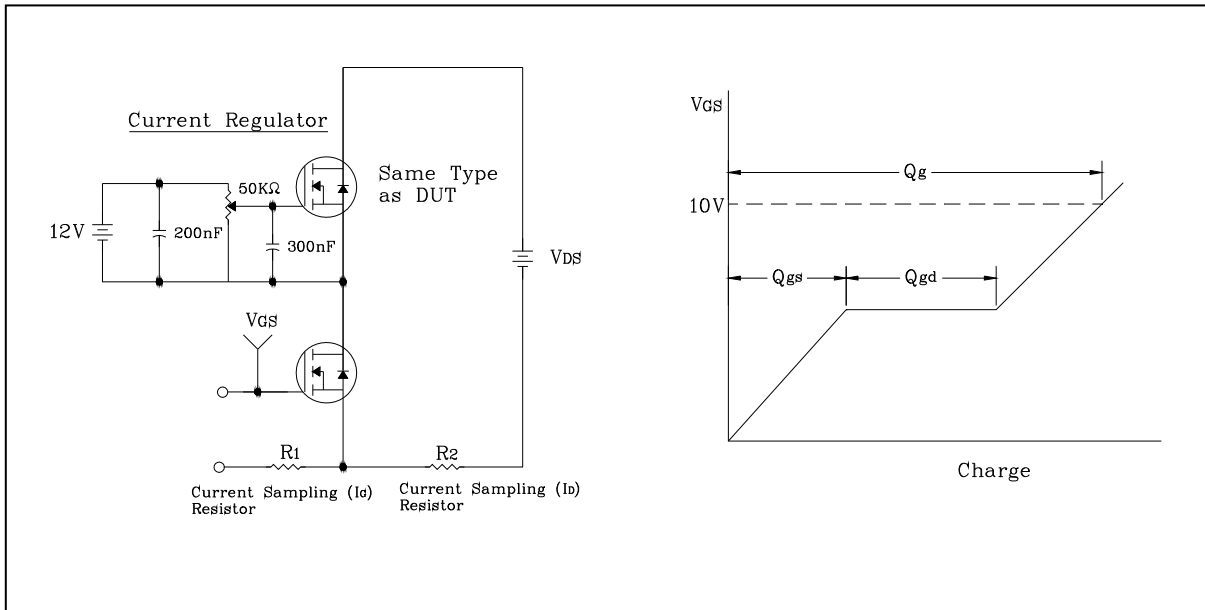


Fig. 12 Resistive Switching Test Circuit & Waveform

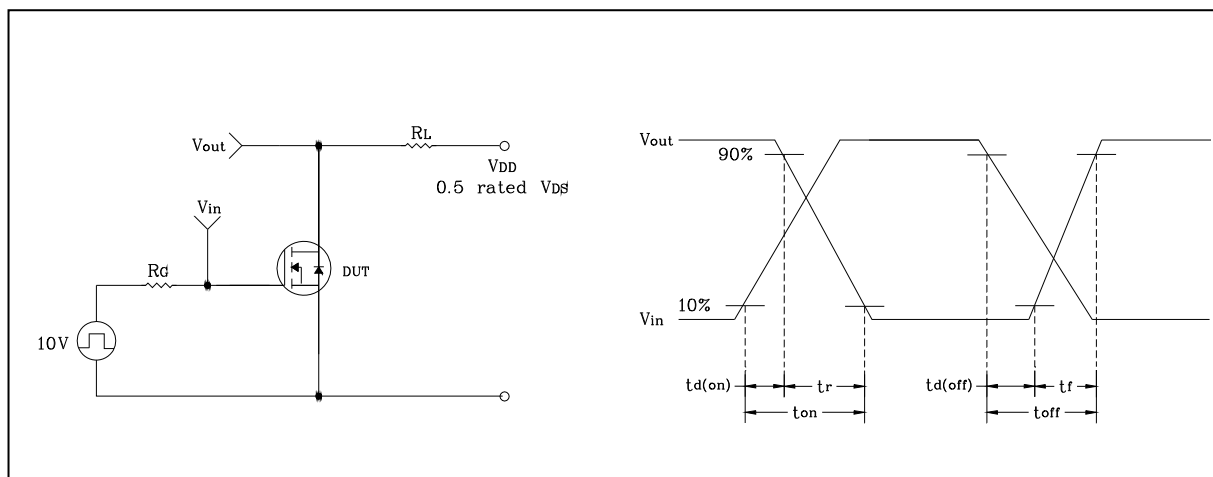


Fig. 13 E_{AS} Test Circuit & Waveform

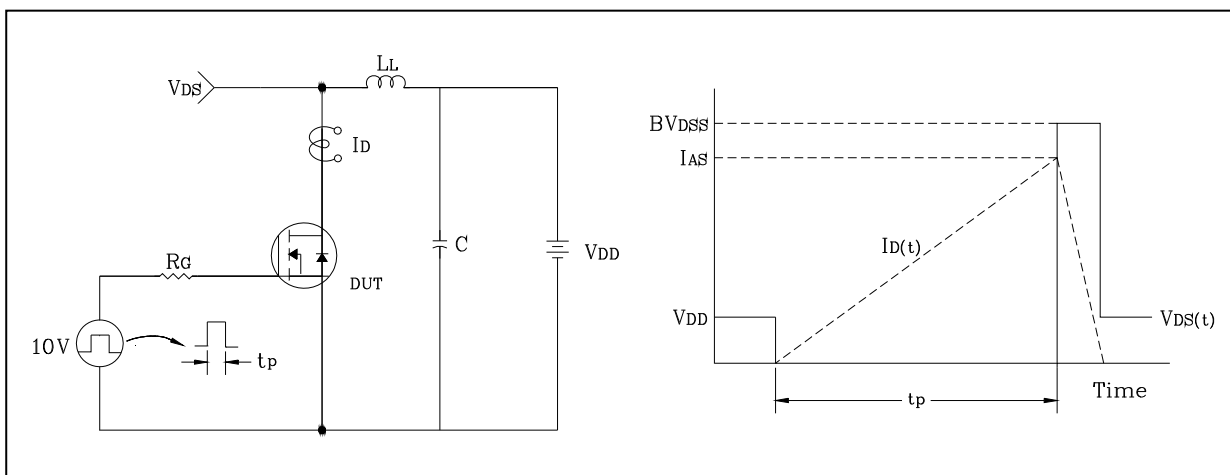
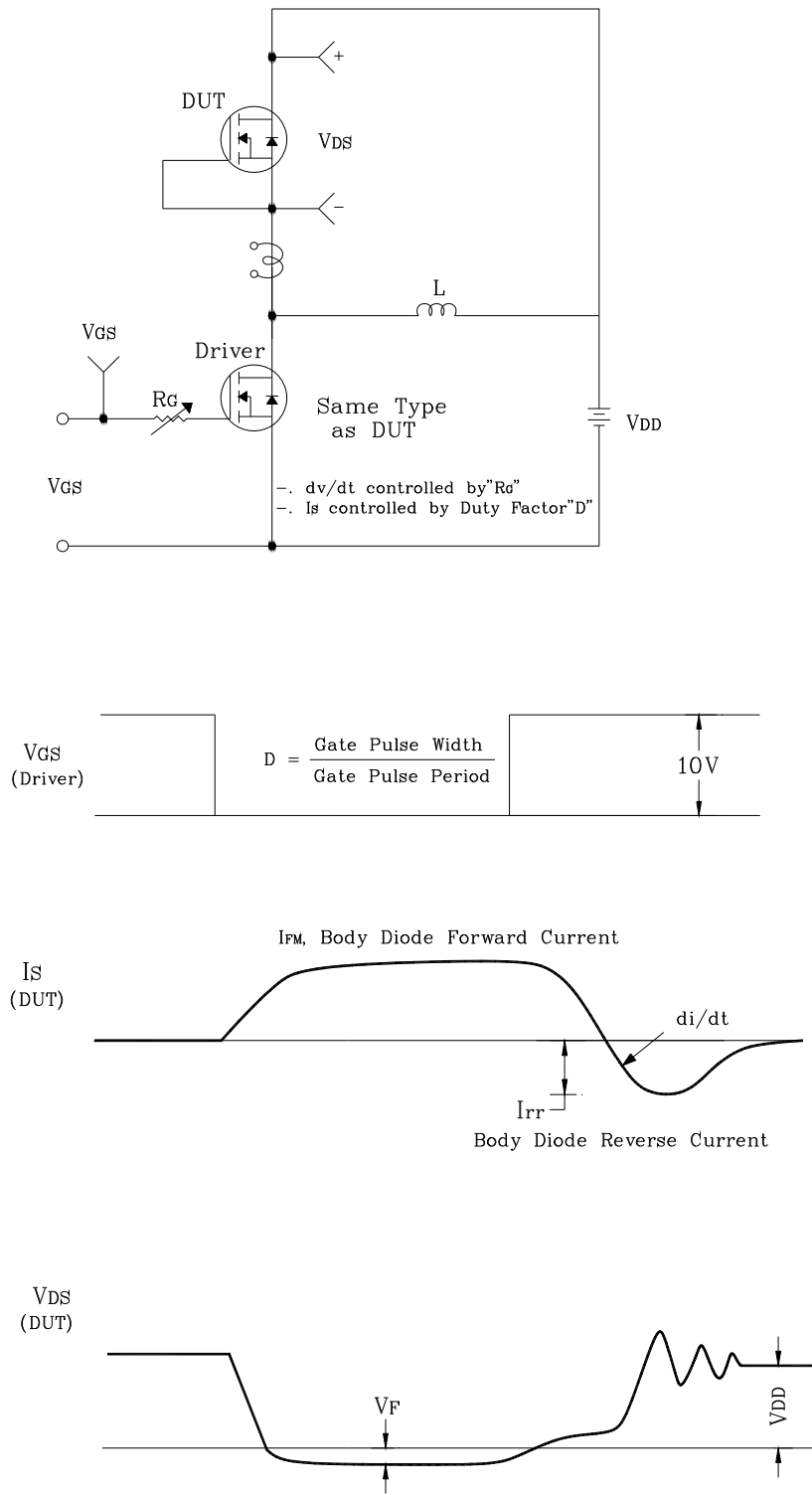
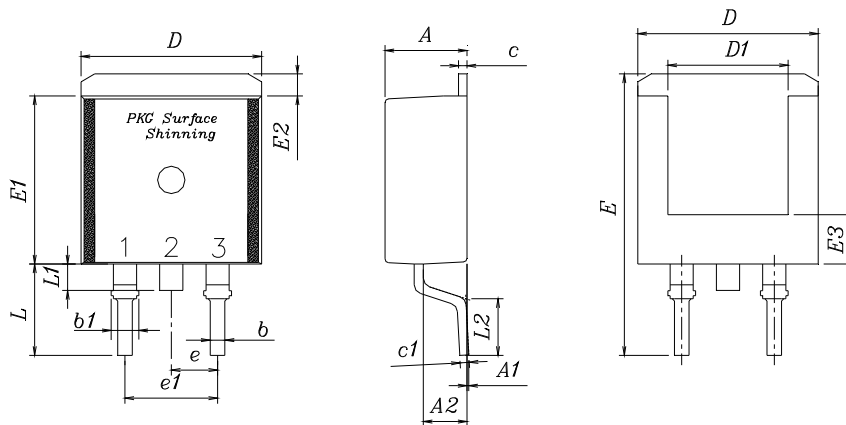


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



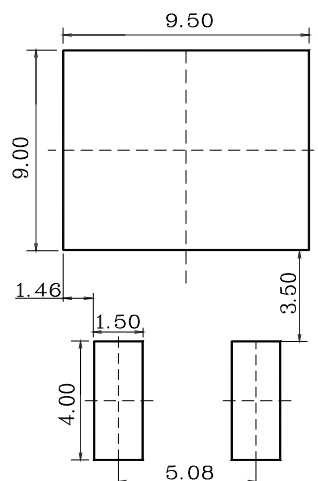
Outline Dimension

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	4.35	4.50	4.65	
A1	—	—	0.15	
A2	2.20	2.40	2.60	
b	0.70	0.80	0.90	
b1	1.17	1.27	1.37	
c	0.40	0.50	0.60	
c1	0.40	0.50	0.60	
D	9.80	10.00	10.20	
D1	6.40	6.60	6.80	
E	15.00	15.40	15.80	
E1	9.05	9.20	9.35	
E2	1.00	1.20	1.40	
E3	2.50	2.70	2.90	
e	2.34	2.54	2.74	
e1	4.88	5.08	5.28	
L	4.60	5.00	5.40	
L1	1.40	1.45	1.50	
L2	2.50	—	—	

※ Recommended Land Pattern [unit: mm]



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